

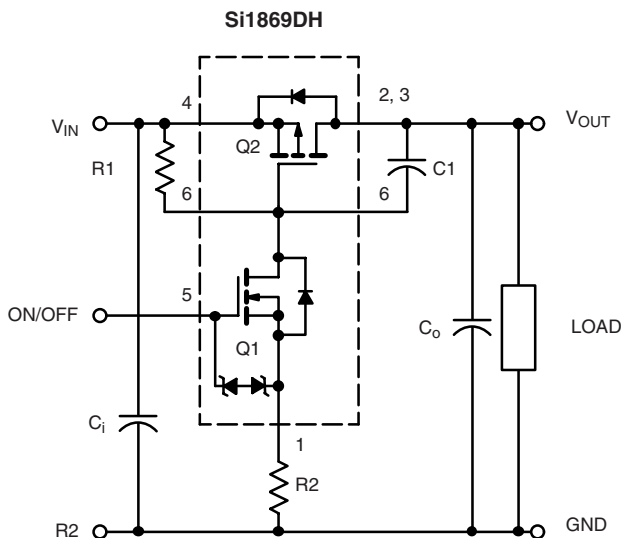
Load Switch with Level-Shift

PRODUCT SUMMARY		
V_{DS2} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
1.8 to 20	0.165 at $V_{IN} = 4.5$ V	± 1.2
	0.222 at $V_{IN} = 2.5$ V	± 1.0
	0.303 at $V_{IN} = 1.8$ V	± 0.7

DESCRIPTION

The Si1869DH includes a p- and n-channel MOSFET in a single SC70-6 package. The low on-resistance p-channel TrenchFET is tailored for use as a load switch. The n-channel, with an external resistor, can be used as a level-shift to drive the p-channel load-switch. The n-channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si1869DH operates on supply lines from 1.8 V to 20 V, and can drive loads up to 1.2 A.

APPLICATION CIRCUITS



COMPONENTS		
R1	Pull-Up Resistor	Typical 10 k Ω to 1 M Ω *
R2	Optional Slew-Rate Control	Typical 0 to 100 k Ω *
C1	Optional Slew-Rate Control	Typical 1000 pF

* Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

FEATURES

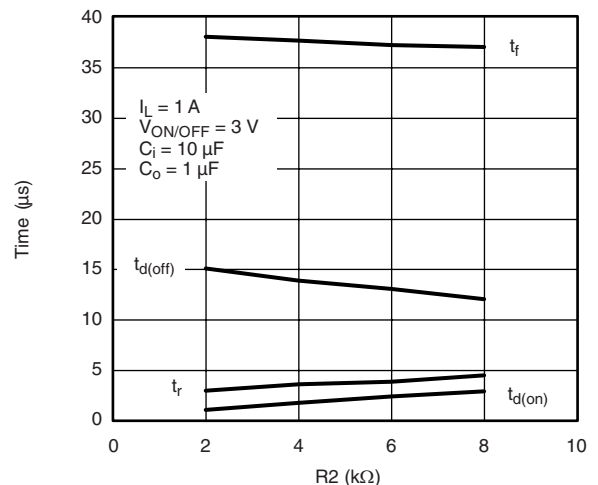
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs: 1.8 V Rated
- ESD Protected: 2000 V On Input Switch, $V_{ON/OFF}$
- 165 m Ω Low $R_{DS(on)}$
- 1.8 to 20 V Input
- 1.5 to 8 V Logic Level Control
- Low Profile, Small Footprint SC70-6 Package
- Adjustable Slew-Rate
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Level Shift for Portable Devices

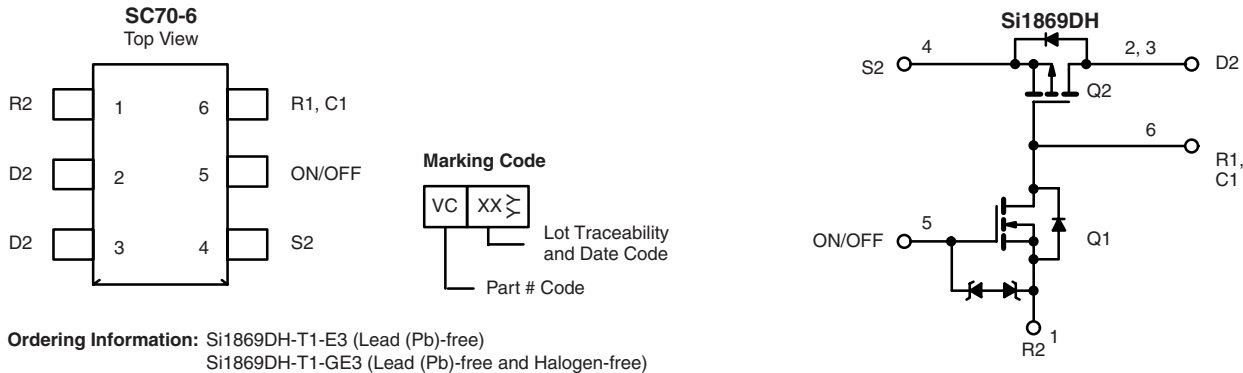


Note: For R2 switching variations with other $V_{IN}/R1$ combinations see Typical Characteristics

Switching Variation
R2 at $V_{IN} = 2.5$ V, R1 = 20 k Ω

The Si1869DH is ideally suited for high-side load switching in portable applications. The integrated n-channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

FUNCTIONAL BLOCK DIAGRAM



Ordering Information: Si1869DH-T1-E3 (Lead (Pb)-free)
Si1869DH-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage (D2-S2)	V_{DS}	- 20	V	
Input Voltage	V_{IN}	20		
ON/OFF Voltage	$V_{ON/OFF}$	8		
Load Current	Continuous ^{a, b}	± 1.2	A	
	Pulsed ^{b, c}	± 3		
Continuous Intrinsic Diode Conduction ^a	I_S	- 0.4	A	
Maximum Power Dissipation ^a	P_D	1.0	W	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$	
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1500 Ω)	ESD	2	kV	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (Continuous Current) ^a	R_{thJA}	100	125	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Foot (Q2)	R_{thJF}	44	55	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF Characteristics						
Reverse Leakage Current	I_{FL}	$V_{IN} = 8\text{ V}, V_{ON/OFF} = 0\text{ V}$			1	μA
Diode Forward Voltage	V_{SD}	$I_S = -0.4\text{ A}$	0.4	0.6	1.1	V
ON Characteristics						
Input Voltage Range	V_{IN}		1.8		20	V
Drain to Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 20			
On-Resistance (P-Channel) at 1 A	$R_{DS(on)}$	$V_{ON/OFF} = 1.5\text{ V}, V_{IN} = 4.5\text{ V}, I_D = 1.2\text{ A}$		0.132	0.165	Ω
		$V_{ON/OFF} = 1.5\text{ V}, V_{IN} = 2.5\text{ V}, I_D = 1.0\text{ A}$		0.177	0.222	
		$V_{ON/OFF} = 1.5\text{ V}, V_{IN} = 1.8\text{ V}, I_D = 0.7\text{ A}$		0.242	0.303	
On-State (P-Channel) Drain-Current	$I_{D(on)}$	$V_{IN-OUT} \leq 0.2\text{ V}, V_{IN} = 5\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1			A
		$V_{IN-OUT} \leq 0.3\text{ V}, V_{IN} = 3\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1			

Notes:

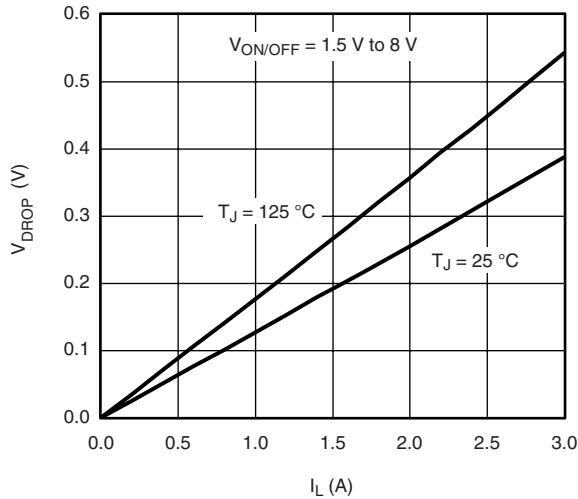
a. Surface mounted on FR4 board.

b. $V_{IN} = 20\text{ V}, V_{ON/OFF} = 8\text{ V}, T_A = 25\text{ }^\circ\text{C}$.

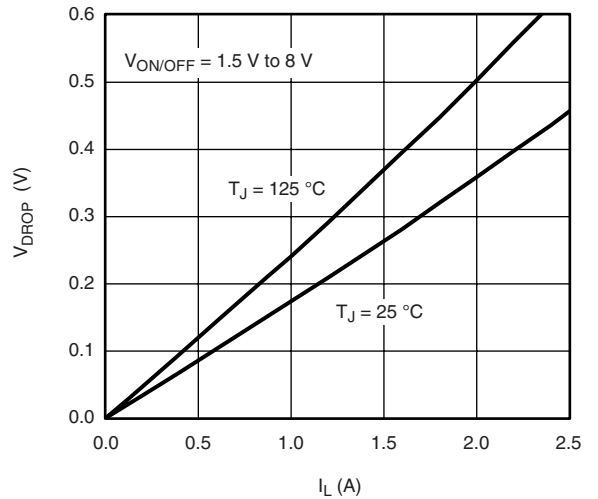
c. Pulse test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

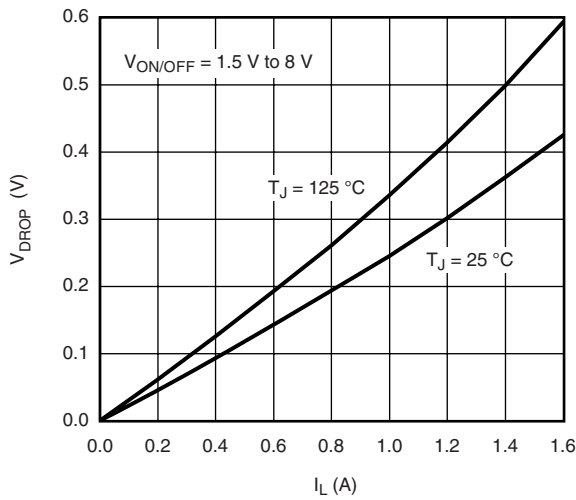
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



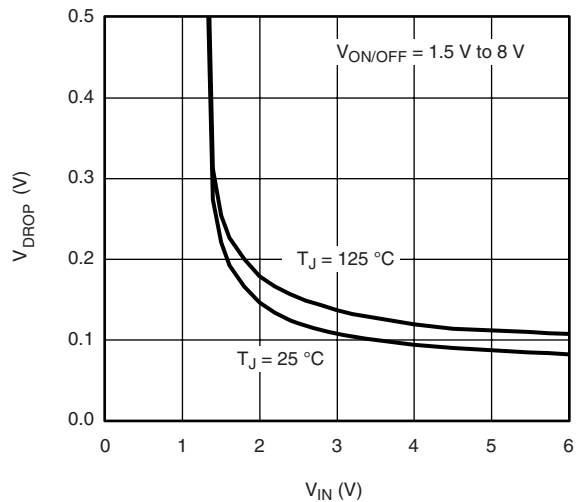
V_{DR}OP vs. I_L at V_{IN} = 4.5 V



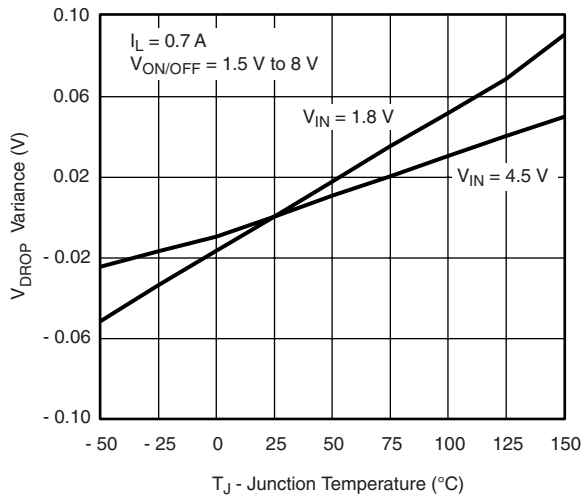
V_{DR}OP vs. I_L at V_{IN} = 2.5 V



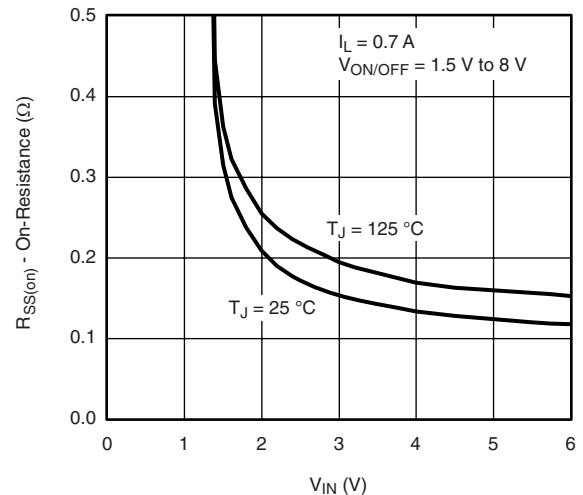
V_{DR}OP vs. I_L at V_{IN} = 1.8 V



V_{DR}OP vs. V_{IN} at I_L = 0.7 A

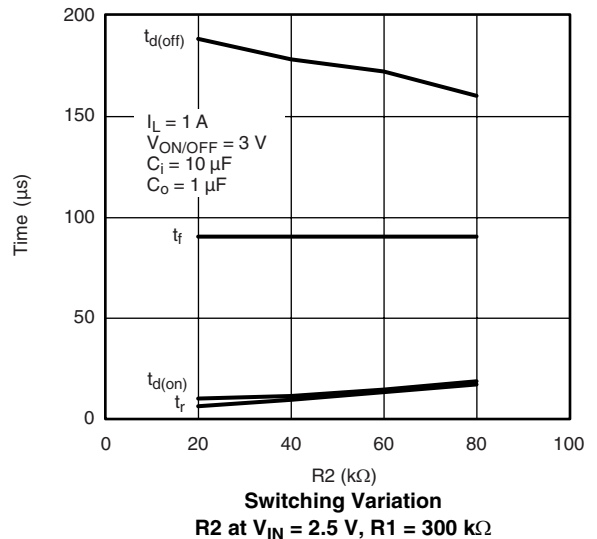
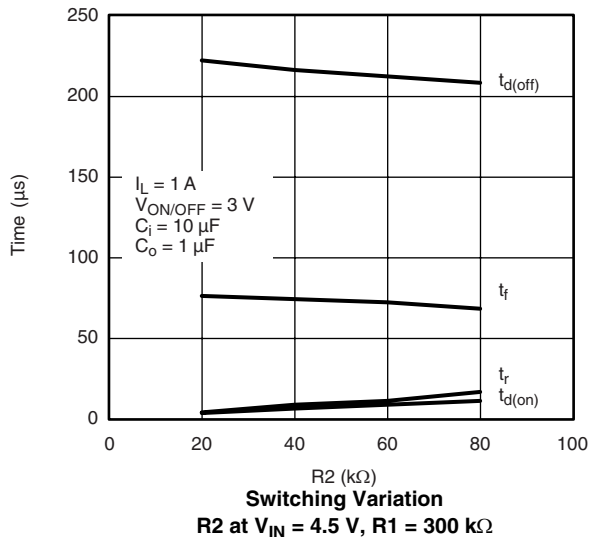
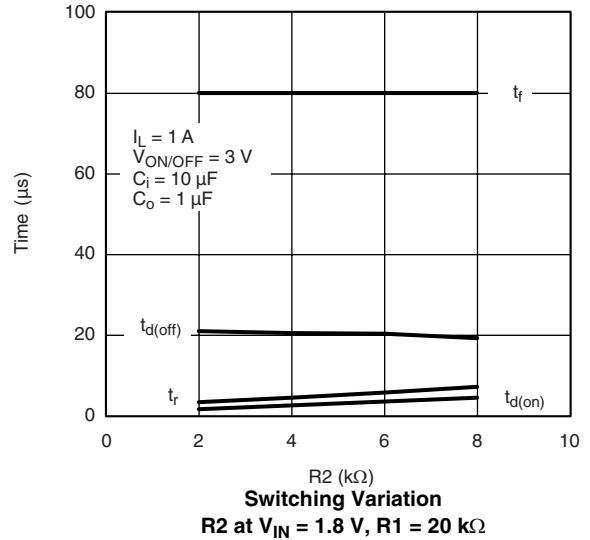
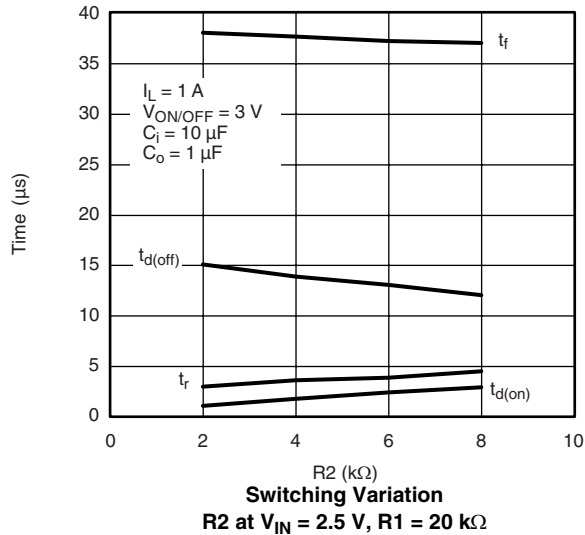
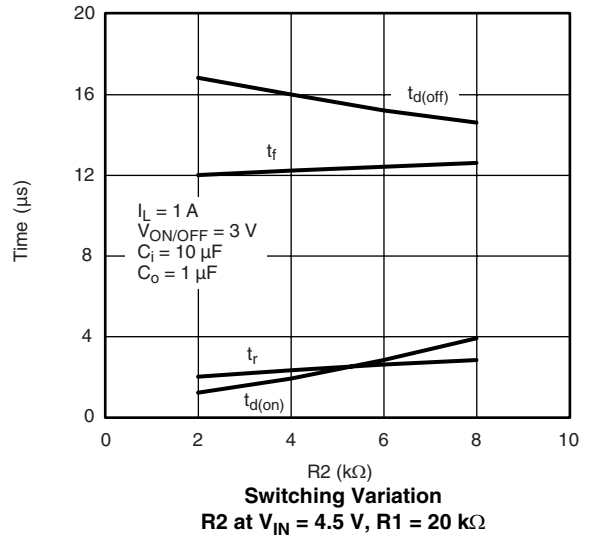
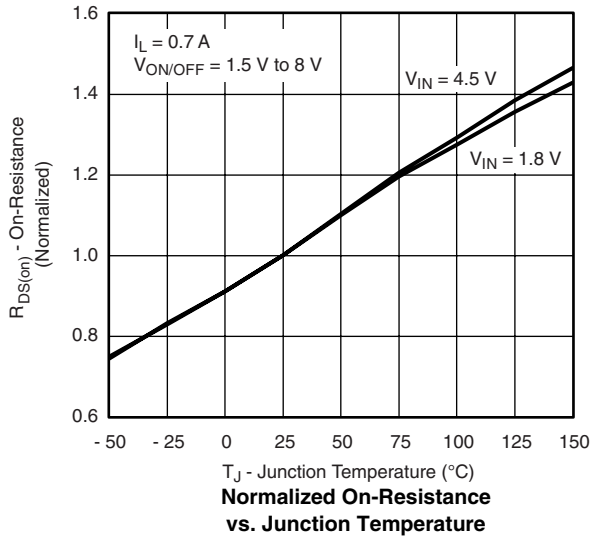


V_{DR}OP Variance vs. Junction Temperature

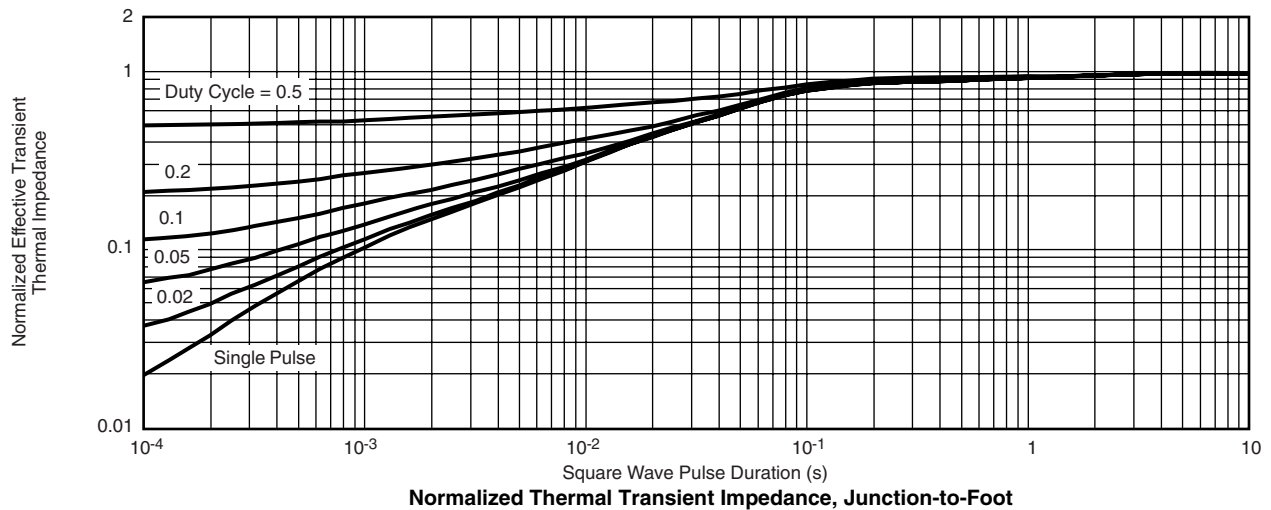
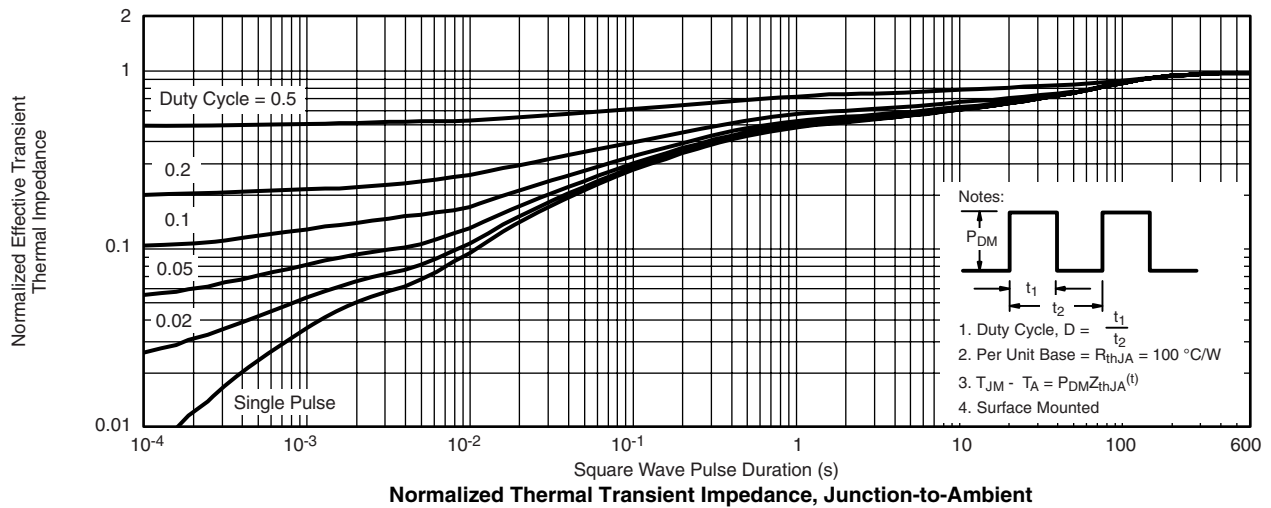
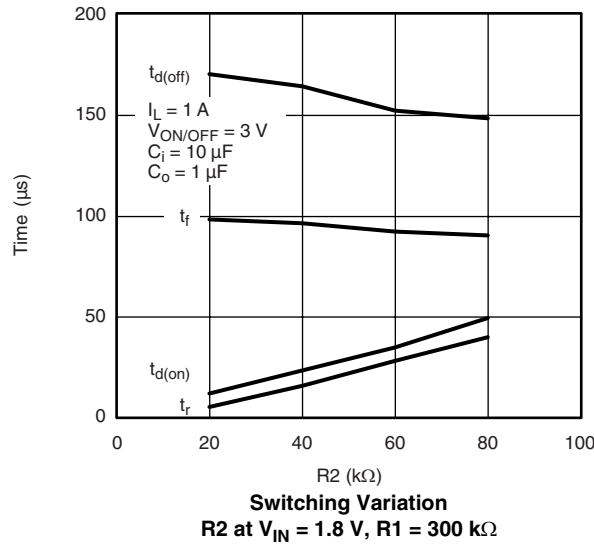


On-Resistance vs. Input Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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SC-70: 6-LEADS



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	-	1.10	0.035	-	0.043
A ₁	-	-	0.10	-	-	0.004
A ₂	0.80	-	1.00	0.031	-	0.039
b	0.15	-	0.30	0.006	-	0.012
c	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
α	7°Nom			7°Nom		

ECN: S-03946—Rev. B, 09-Jul-01
DWG: 5550

Dual-Channel LITTLE FOOT® 6-Pin SC-70 MOSFET Copper Leadframe Version Recommended Pad Pattern and Thermal Performance

INTRODUCTION

The new dual 6-pin SC-70 package with a copper leadframe enables improved on-resistance values and enhanced thermal performance as compared to the existing 3-pin and 6-pin packages with Alloy 42 leadframes. These devices are intended for small to medium load applications where a miniaturized package is required. Devices in this package come in a range of on-resistance values, in n-channel and p-channel versions. This technical note discusses pin-outs, package outlines, pad patterns, evaluation board layout, and thermal performance for the dual-channel version.

PIN-OUT

Figure 1 shows the pin-out description and Pin 1 identification for the dual-channel SC-70 device in the 6-pin configuration. Both n- and p-channel devices are available in this package – the drawing example below illustrates the p-channel device.

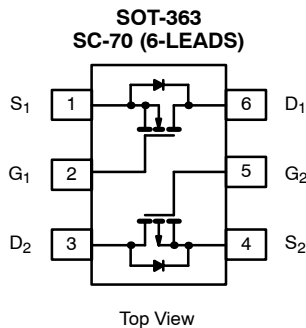


FIGURE 1.

For package dimensions see outline drawing SC-70 (6-Leads) (<http://www.vishay.com/doc?71154>)

BASIC PAD PATTERNS

See Application Note 826, *Recommended Minimum Pad Patterns With Outline Drawing Access for Vishay Siliconix MOSFETs*, (<http://www.vishay.com/doc?72286>) for the SC-70 6-pin basic pad layout and dimensions. This pad pattern is sufficient for the low-power applications for which this package is intended. Increasing the drain pad pattern (Figure 2) yields a reduction in thermal resistance and is a preferred footprint.

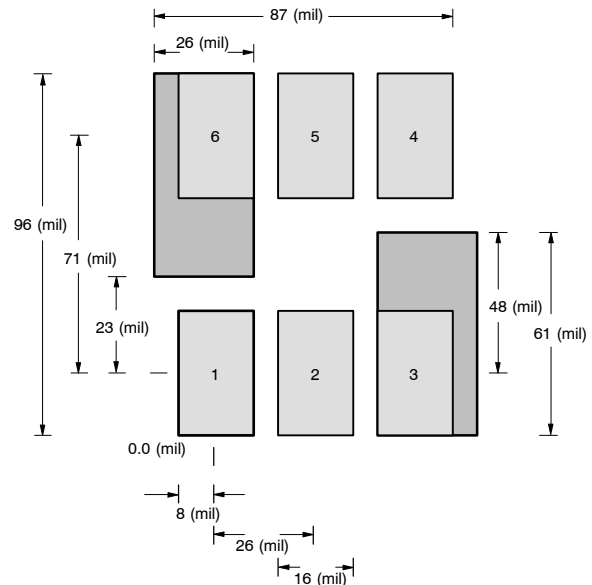


FIGURE 2. SC-70 (6 leads) Dual

EVALUATION BOARD FOR THE DUAL-CHANNEL SC70-6

The 6-pin SC-70 evaluation board (EVB) shown in Figure 3 measures 0.6 in. by 0.5 in. The copper pad traces are the same as described in the previous section, *Basic Pad Patterns*. The board allows for examination from the outer pins to the 6-pin DIP connections, permitting test sockets to be used in evaluation testing.

The thermal performance of the dual 6-pin SC-70 has been measured on the EVB, comparing both the copper and Alloy 42 leadframes. This test was then repeated using the 1-inch² PCB with dual-side copper coating.

A helpful way of displaying the thermal performance of the 6-pin SC-70 dual copper leadframe is to compare it to the traditional Alloy 42 version.

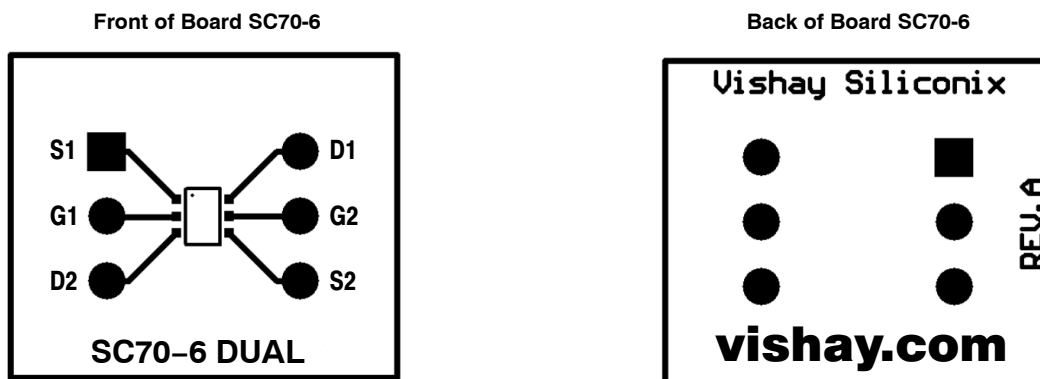


FIGURE 3.

THERMAL PERFORMANCE

Junction-to-Foot Thermal Resistance (the Package Performance)

Thermal performance for the dual SC-70 6-pin package is measured as junction-to-foot thermal resistance, in which the “foot” is the drain lead of the device as it connects with the body. The junction-to-foot thermal resistance for this device is typically 80°C/W, with a maximum thermal resistance of approximately 100°C/W. This data compares favorably with another compact, dual-channel package – the dual TSOP-6 – which features a typical thermal resistance of 75°C/W and a maximum of 90°C/W.

Power Dissipation

The typical $R_{\theta JA}$ for the dual-channel 6-pin SC-70 with a copper leadframe is 224°C/W steady-state, compared to 413°C/W for the Alloy 42 version. All figures are based on the 1-inch² FR4 test board. The following example shows how the thermal resistance impacts power dissipation for the dual 6-pin SC-70 package at varying ambient temperatures.

Alloy 42 Leadframe

ALLOY 42 LEADFRAME	
Room Ambient 25 °C	Elevated Ambient 60 °C
$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$	$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$
$P_D = \frac{150^{\circ}C - 25^{\circ}C}{413^{\circ}C/W}$	$P_D = \frac{150^{\circ}C - 60^{\circ}C}{413^{\circ}C/W}$
$P_D = 303 \text{ mW}$	$P_D = 218 \text{ mW}$

COOPER LEADFRAME	
Room Ambient 25 °C	Elevated Ambient 60 °C
$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$	$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$
$P_D = \frac{150^{\circ}C - 25^{\circ}C}{224^{\circ}C/W}$	$P_D = \frac{150^{\circ}C - 60^{\circ}C}{224^{\circ}C/W}$
$P_D = 558 \text{ mW}$	$P_D = 402 \text{ mW}$

Although they are intended for low-power applications, devices in the 6-pin SC-70 dual-channel configuration will handle power dissipation in excess of 0.5 W.

TESTING

To further aid the comparison of copper and Alloy 42 leadframes, Figures 4 and 5 illustrate the dual-channel 6-pin SC-70 thermal performance on two different board sizes and pad patterns. The measured steady-state values of $R_{\theta JA}$ for the dual 6-pin SC-70 with varying leadframes are as follows:

LITTLE FOOT 6-PIN SC-70		
	Alloy 42	Copper
1) Minimum recommended pad pattern on the EVB board (see Figure 3).	518°C/W	344°C/W
2) Industry standard 1-inch ² PCB with maximum copper both sides.	413°C/W	224°C/W

The results indicate that designers can reduce thermal resistance (θ_{JA}) by 34% simply by using the copper leadframe device as opposed to the Alloy 42 version. In this example, a 174°C/W reduction was achieved without an increase in board area. If an increase in board size is feasible, a further 120°C/W reduction can be obtained by utilizing a 1-inch². PCB area.

The Dual copper leadframe versions have the following suffix:

Dual: Si19xxEDH
 Compl.: Si15xxEDH

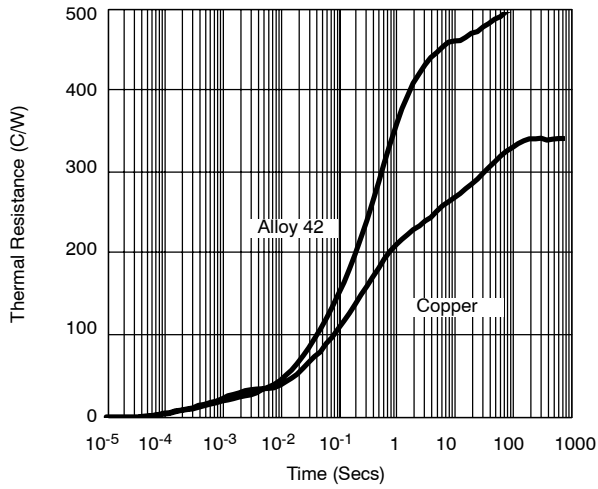


FIGURE 4. Dual SC70-6 Thermal Performance on EVB

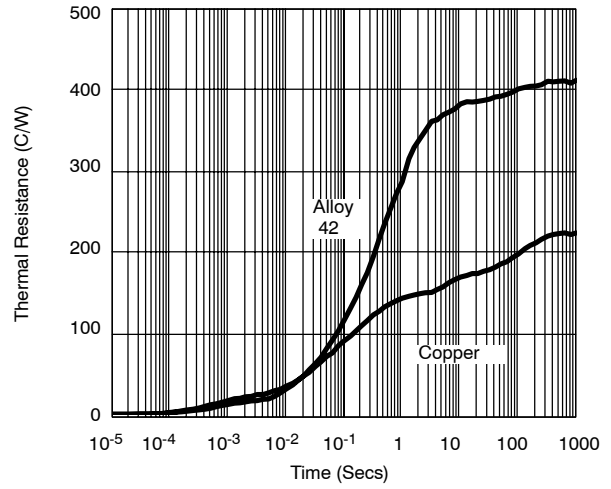


FIGURE 5. Dual SC70-6 Comparison on 1-inch² PCB

RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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